

PHOTOCOUPLER PS2581L1,PS2581L2

LONG CREEPAGE TYPE HIGH ISOLATION VOLTAGE 4-PIN PHOTOCOUPLER

-NEPOC Series-

DESCRIPTION

The PS2581L1, PS2581L2 are optically coupled isolators containing a GaAs light emitting diode and an NPN silicon phototransistor in a plastic DIP (Dual In-line Package).

Creepage distance and clearance of leads are over 8 millimeters.

The PS2581L2 is lead bending type (Gull-wing) for surface mounting.

FEATURES

- Long creepage and clearance distance (8 mm)
- High isolation voltage (BV = 5 000 Vr.m.s.)
- High collector to emitter voltage (VCEO = 80 V)
- High-speed switching (tr = 3 μ s TYP., tr = 5 μ s TYP.)
- High current transfer ratio (CTR = 200 % TYP.)
- UL approved: File No. E72422 (S)
- CSA approved: No. CA101391
- BSI approved: No. 8243/8244
- NEMKO approved: No. P97103006
- DEMKO approved: No. 307269
- SEMKO approved: No. 9741154/01
- FIMKO approved: No. 018277
- VDE0884 approved

ORDERING INFORMATION (Solder Contains Lead)

Part Number	Package	Safety Standard Approval	Application Part Number *1
PS2581L1	4-pin DIP	UL, CSA, BSI, NEMKO, DEMKO,	PS2581L1
PS2581L2	4-pin DIP (lead bending surface mount)	SEMKO, FIMKO, VDE approved	PS2581L2
PS2581L2-E3, E4	4-pin DIP taping		

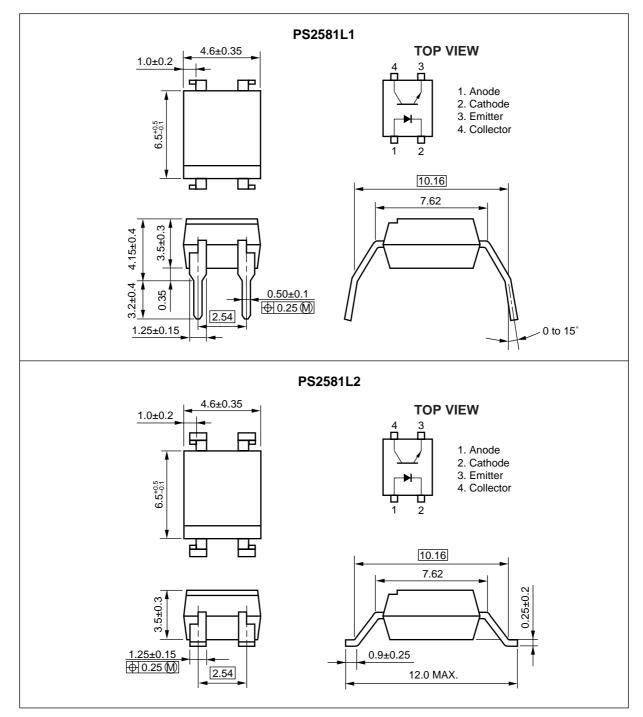
*1 As applying to Safety Standard, following part number should be used.

ORDERING INFORMATION (Pb-Free)

Part Number	Package	Safety Standard Approval	Application Part Number *1
PS2581L1-A	4-pin DIP	UL, CSA, BSI, NEMKO, DEMKO,	PS2581L1
PS2581L2-A	4-pin DIP (lead bending surface mount)	SEMKO, FIMKO, VDE approved	PS2581L2
PS2581L2-E3, E4-A	4-pin DIP taping		

*1 As applying to Safety Standard, following part number should be used.

The information in this document is subject to change without notice. Before using this document, please confirm that this is the latest version.



PACKAGE DIMENSIONS (in millimeters)

PHOTOCOUPLER CONSTRUCTION

Parameter	Unit (MIN.)
Air Distance	8 mm
Outer Creepage Distance	8 mm
Inner Creepage Distance	4 mm
Isolation Distance	0.4 mm

Parameter		Symbol	Ratings	Unit
Diode	Forward Current (DC)	lf	80	mA
	Reverse Voltage	VR	6	V
	Power Dissipation Derating	⊿P₀/°C	1.5	mW/°C
	Power Dissipation	PD	150	mW
	Peak Forward Current ^{*1}	IFP	1	А
Transistor	Collector to Emitter Voltage	Vceo	80	V
	Emitter to Collector Voltage	Veco	7	V
	Collector Current	lc	50	mA
	Power Dissipation Derating	⊿Pc/°C	1.5	mW/°C
	Power Dissipation	Pc	150	mW
Isolation Voltage *2		BV	5 000	Vr.m.s.
Operating Ambient Temperature		TA	–55 to +100	°C
Storage Temperature		Tstg	-55 to +150	°C

ABSOLUTE MAXIMUM RATINGS (TA = 25 °C, unless otherwise specified)

*1 PW = 100 µs, Duty Cycle = 1 %

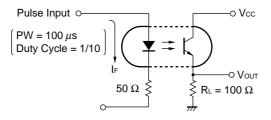
*2 AC voltage for 1 minute at $T_A = 25$ °C, RH = 60 % between input and output

ELECTRICAL CHARACTERISTICS (TA = 25 °C)

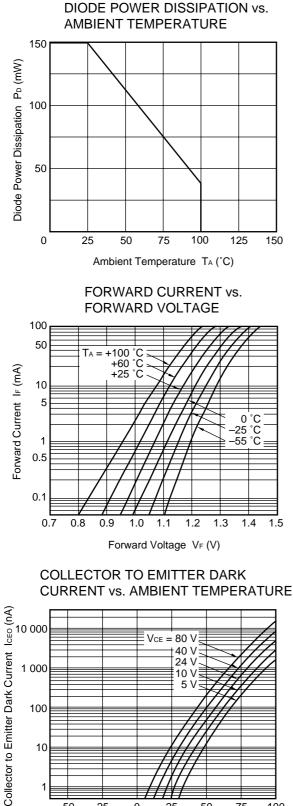
Parameter		Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Diode	Forward Voltage	VF	IF = 10 mA		1.17	1.4	V
	Reverse Current	Ir	V _R = 5 V			5	μA
	Terminal Capacitance	Ct	V = 0 V, f = 1.0 MHz		50		pF
Transistor	Collector to Emitter Dark Current	ICEO	V _{CE} = 80 V, I _F = 0 mA			100	nA
Coupled	Current Transfer Ratio (Ic/IF) *1	CTR	IF = 5 mA, VCE = 5 V	80	200	400	%
	Collector Saturation Voltage	VCE(sat)	IF = 10 mA, Ic = 2 mA			0.3	V
	Isolation Resistance	Ri-o	VI-0 = 1.0 kVDC	10 ¹¹			Ω
	Isolation Capacitance	CI-O	V = 0 V, f = 1.0 MHz		0.5		pF
	Rise Time *2	tr	Vcc = 10 V, Ic = 2 mA,		3		μS
	Fall Time ^{*2}	tr	R∟ = 100 Ω		5		

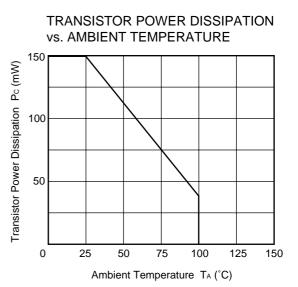
*1 CTR rank

- L : 200 to 400 (%)
- M: 80 to 240 (%)
- D : 100 to 300 (%)
- H : 80 to 160 (%)
- W : 130 to 260 (%)
- N : 80 to 400 (%)
- *2 Test circuit for switching time

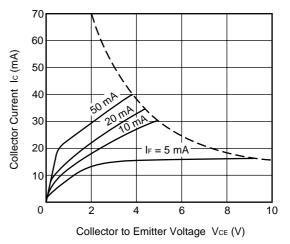


TYPICAL CHARACTERISTICS (TA = 25 °C, unless otherwise specified)

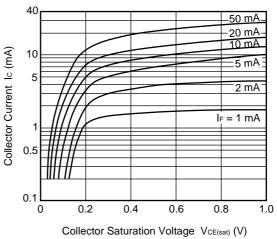




COLLECTOR CURRENT vs. COLLECTOR TO EMITTER VOLTAGE



COLLECTOR CURRENT vs. COLLECTOR SATURATION VOLTAGE



50

75

100

25 Ambient Temperature T_A (°C)

-50

-25

0

0.5

1

Forward Current IF (mA)

5 10

5k 10k

l⊧ = 5 mÅ T_A = 25 °C

I⊧ = 5 mÅ T_A = 60 °C

10⁴

10³

Time (Hr)

Load Resistance $R_{L}(\Omega)$

50

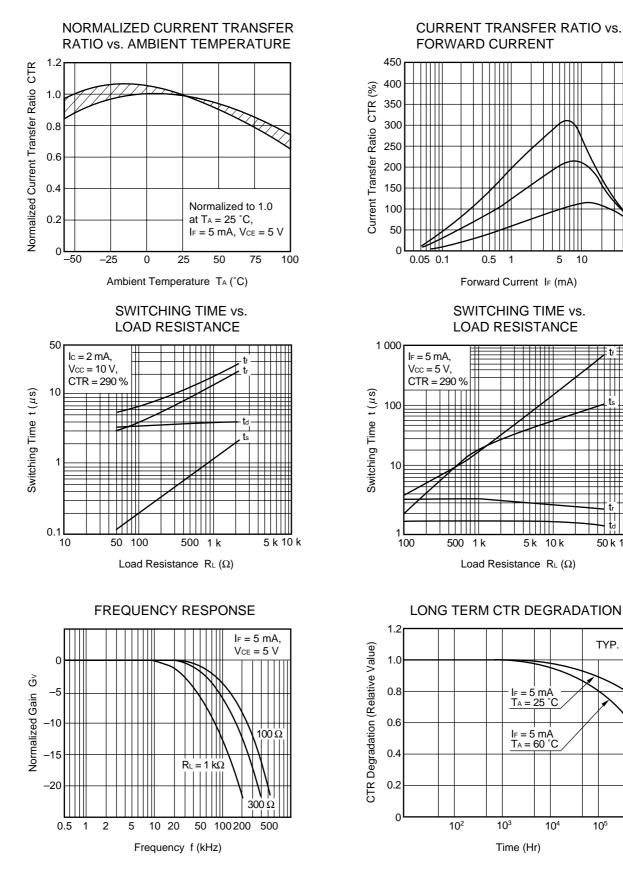
ts

tr td

TYP.

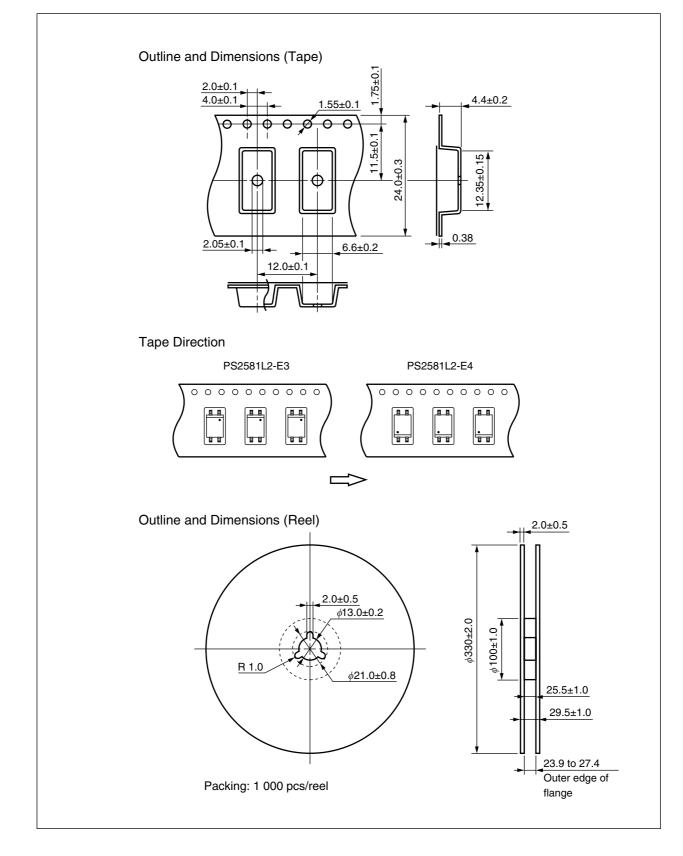
10⁵

50 k 100 k



Remark The graphs indicate nominal characteristics.

* TAPING SPECIFICATIONS (in millimeters)



***** NOTES ON HANDLING

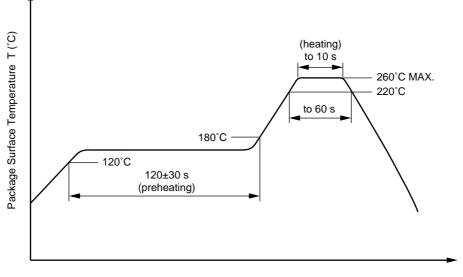
1. Recommended soldering conditions

(1) Infrared reflow soldering

- Peak reflow temperature
- Time of peak reflow temperature
- Time of temperature higher than 220°C
- Time to preheat temperature from 120 to 180°C
- Number of reflows
- Flux

260°C or below (package surface temperature) 10 seconds or less 60 seconds or less 120±30 s Three Rosin flux containing small amount of chlorine (The flux with a maximum chlorine content of 0.2 Wt% is recommended.)

Recommended Temperature Profile of Infrared Reflow



Time (s)

(2) Wave soldering

- Temperature 260°C or below (molten solder temperature)
- Time 10 seconds or less
- Preheating conditions 120°C or below (package surface temperature)
- Number of times One (Allowed to be dipped in solder including plastic mold portion.)
- Flux Rosin flux containing small amount of chlorine (The flux with a maximum chlorine content of 0.2 Wt% is recommended.)

(3) Cautions

Fluxes

Avoid removing the residual flux with freon-based and chlorine-based cleaning solvent.

2. Cautions regarding noise

Be aware that when voltage is applied suddenly between the photocoupler's input and output or between collector-emitters at startup, the output side may enter the on state, even if the voltage is within the absolute maximum ratings.

★ USAGE CAUTIONS

- 1. Protect against static electricity when handling.
- 2. Avoid storage at a high temperature and high humidity.

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SPECIFICATION OF VDE MARKS LICENSE DOCUMENT (VDE0884)

Parameter	Symbol	Speck	Unit
Application classification (DIN VDE 0109) for rated line voltages \leq 300 Vr.m.s. for rated line voltages \leq 600 Vr.m.s.		IV III	
Climatic test class (DIN IEC 68 Teil 1/09.80)		55/100/21	
Dielectric strength maximum operating isolation voltage. Test voltage (partial discharge test procedure a for type test and random test) $U_{pr} = 1.2 \times U_{IORM}, P_d < 5 pC$	Uiorm Upr	890 1 068	V _{peak} V _{peak}
Test voltage (partial discharge test procedure b for all devices test) U_{pr} = 1.6 \times U_{\text{IORM}}, P_{\text{d}} < 5 \ pC	Upr	1 424	V _{peak}
Highest permissible overvoltage	Utr	8 000	V _{peak}
Degree of pollution (DIN VDE 0109)		2	
Clearance distance		> 8.0	mm
Creepage distance		> 8.0	mm
Comparative tracking index (DIN IEC 112/VDE 0303 part 1)	СТІ	175	
Material group (DIN VDE 0109)		lll a	
Storage temperature range	Tstg	–55 to +150	°C
Operating temperature range	TA	–55 to +100	°C
Isolation resistance, minimum value $V_{IO} = 500 \text{ V dc at } T_A = 25 \text{ °C}$ $V_{IO} = 500 \text{ V dc at } T_A MAX. at least 100 \text{ °C}$	Ris MIN. Ris MIN.	10 ¹² 10 ¹¹	Ω Ω
Safety maximum ratings (maximum permissible in case of fault, see thermal derating curve) Package temperature Current (input current IF, Psi = 0) Power (output or total power dissipation) Isolation resistance	Tsi Isi Psi	175 400 700	°C mA mW
$V_{IO} = 500 \text{ V dc at } T_A = 175 \text{ °C } (Tsi)$	Ris MIN.	10 ⁹	Ω



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Subject: Compliance with EU Directives

CEL certifies, to its knowledge, that semiconductor and laser products detailed below are compliant with the requirements of European Union (EU) Directive 2002/95/EC Restriction on Use of Hazardous Substances in electrical and electronic equipment (RoHS) and the requirements of EU Directive 2003/11/EC Restriction on Penta and Octa BDE.

CEL Pb-free products have the same base part number with a suffix added. The suffix –A indicates that the device is Pb-free. The –AZ suffix is used to designate devices containing Pb which are exempted from the requirement of RoHS directive (*). In all cases the devices have Pb-free terminals. All devices with these suffixes meet the requirements of the RoHS directive.

This status is based on CEL's understanding of the EU Directives and knowledge of the materials that go into its products as of the date of disclosure of this information.

Restricted Substance per RoHS	Concentration Limit per RoHS (values are not yet fixed)	Concentration contained in CEL devices	
Lead (Pb)	< 1000 PPM	-A -AZ Not Detected (*)	
Mercury	< 1000 PPM	Not Detected	
Cadmium	< 100 PPM	Not Detected	
Hexavalent Chromium	< 1000 PPM	Not Detected	
РВВ	< 1000 PPM	Not Detected	
PBDE	< 1000 PPM	Not Detected	

If you should have any additional questions regarding our devices and compliance to environmental standards, please do not hesitate to contact your local representative.

In no event shall CEL's liability arising out of such information exceed the total purchase price of the CEL part(s) at issue sold by CEL to customer on an annual basis.

See CEL Terms and Conditions for additional clarification of warranties and liability.

Important Information and Disclaimer: Information provided by CEL on its website or in other communications concerting the substance content of its products represents knowledge and belief as of the date that it is provided. CEL bases its knowledge and belief on information provided by third parties and makes no representation or warranty as to the accuracy of such information. Efforts are underway to better integrate information from third parties. CEL has taken and continues to take reasonable steps to provide representative and accurate information but may not have conducted destructive testing or chemical analysis on incoming materials and chemicals. CEL and CEL suppliers consider certain information to be proprietary, and thus CAS numbers and other limited information may not be available for release.